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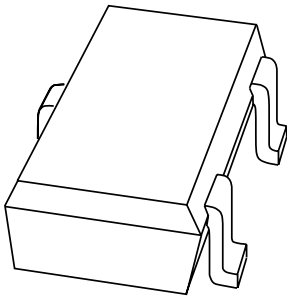
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Kind regards,

Team Nexperia

DATA SHEET



BC849W; BC850W NPN general purpose transistors

Product data sheet
Supersedes data of 1997 Jun 20

1999 Apr 12

NPN general purpose transistors

BC849W; BC850W

FEATURES

- Low current (max. 100 mA)
- Low voltage (max. 45 V).

APPLICATIONS

- Low noise stages in tape recorders, hi-fi amplifiers and other audio-frequency equipment.

DESCRIPTION

NPN transistor in a SOT323 plastic package.
PNP complements: BC859W and BC860W.

MARKING

TYPE NUMBER	MARKING CODE ⁽¹⁾	TYPE NUMBER	MARKING CODE ⁽¹⁾
BC849BW	2B*	BC850BW	2F*
BC849CW	2C*	BC850CW	2G*

Note

- * = - : Made in Hong Kong.
* = t : Made in Malaysia.

PINNING

PIN	DESCRIPTION
1	base
2	emitter
3	collector

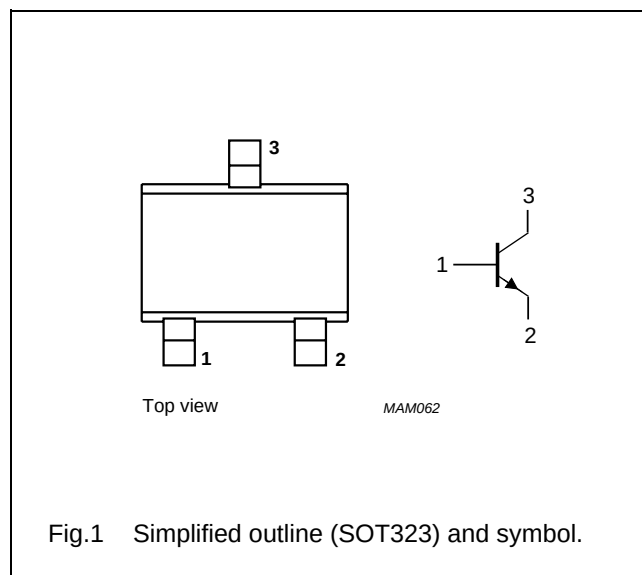


Fig.1 Simplified outline (SOT323) and symbol.

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{CBO}	collector-base voltage	open emitter			
	BC849W		—	30	V
	BC850W		—	50	V
V_{CEO}	collector-emitter voltage	open base			
	BC849W		—	30	V
	BC850W		—	45	V
V_{EBO}	emitter-base voltage	open collector	—	5	V
I_C	collector current (DC)		—	100	mA
I_{CM}	peak collector current		—	200	mA
I_{BM}	peak base current		—	200	mA
P_{tot}	total power dissipation	$T_{amb} \leq 25\text{ }^{\circ}\text{C}$; note 1	—	200	mW
T_{stg}	storage temperature		−65	+150	$^{\circ}\text{C}$
T_j	junction temperature		—	150	$^{\circ}\text{C}$
T_{amb}	operating ambient temperature		−65	+150	$^{\circ}\text{C}$

Note

1. Transistor mounted on an FR4 printed-circuit board.

NPN general purpose transistors

BC849W; BC850W

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th\ j-a}$	thermal resistance from junction to ambient	note 1	625	K/W

Note

1. Transistor mounted on an FR4 printed-circuit board.

CHARACTERISTICS

$T_{amb} = 25\text{ }^{\circ}\text{C}$ unless otherwise specified.

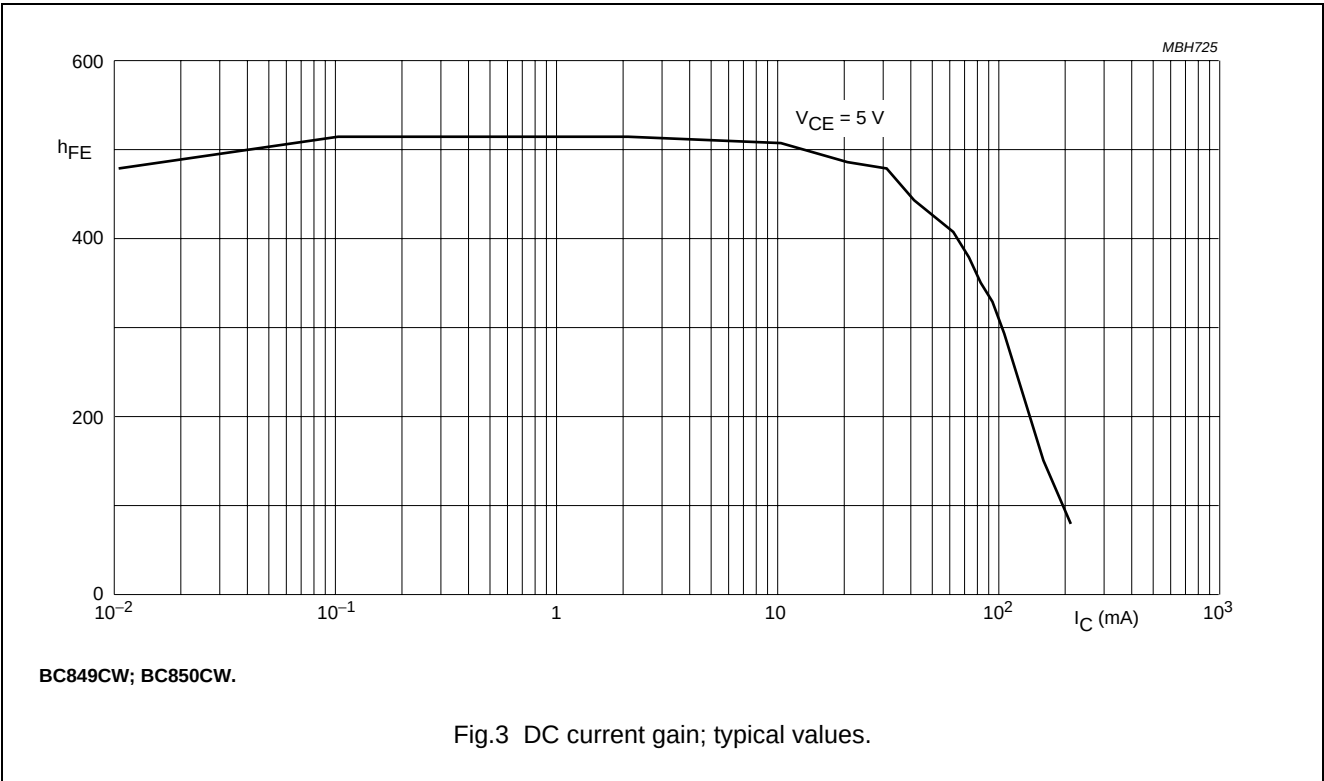
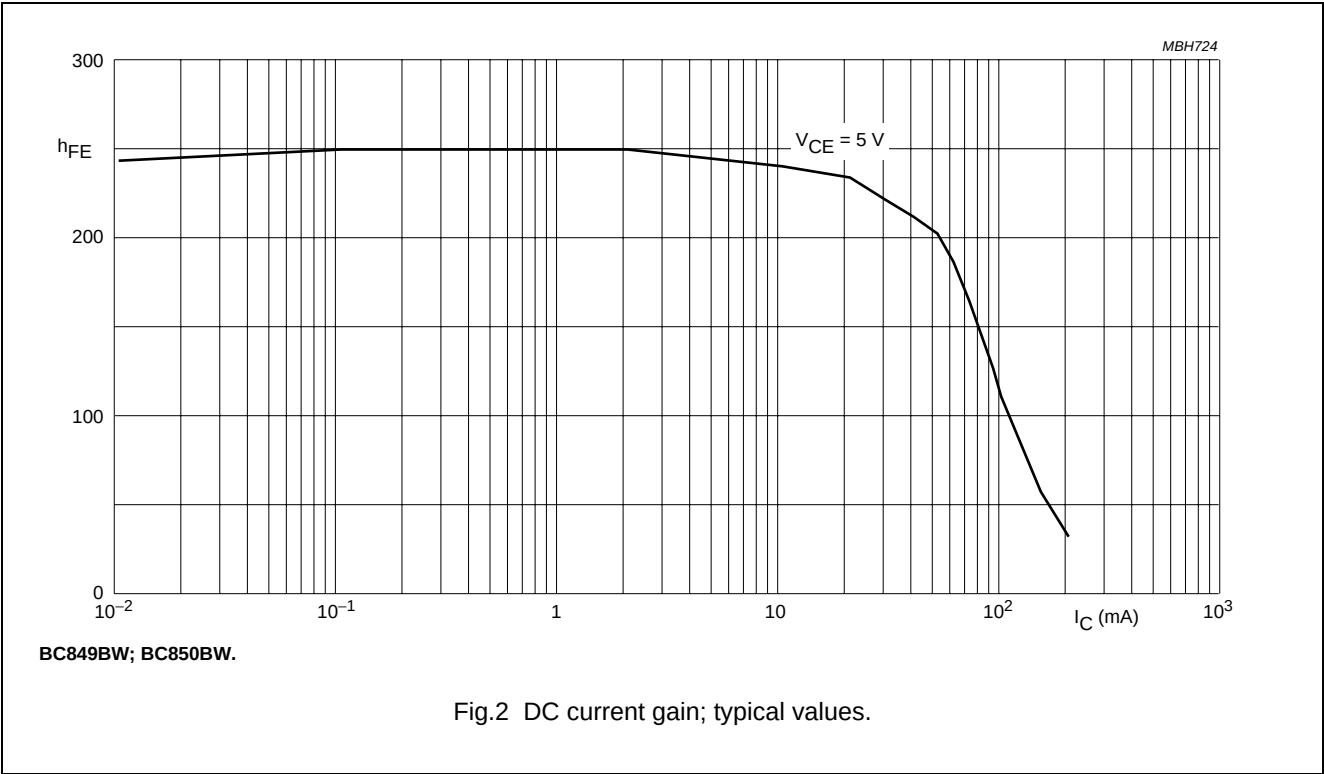
SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I_{CBO}	collector cut-off current	$I_E = 0; V_{CB} = 30\text{ V}$	–	–	15	nA
		$I_E = 0; V_{CB} = 30\text{ V}; T_j = 150\text{ }^{\circ}\text{C}$	–	–	5	μA
I_{EBO}	emitter cut-off current	$I_C = 0; V_{EB} = 5\text{ V}$	–	–	100	nA
h_{FE}	DC current gain BC849BW; BC850BW BC849CW; BC850CW	$I_C = 2\text{ mA}; V_{CE} = 5\text{ V};$ see Figs 2 and 3	200	–	450	
			420	–	800	
V_{CEsat}	collector-emitter saturation voltage	$I_C = 10\text{ mA}; I_B = 0.5\text{ mA}$	–	–	250	mV
		$I_C = 100\text{ mA}; I_B = 5\text{ mA};$ note 1	–	–	600	mV
V_{BE}	base-emitter voltage	$I_C = 2\text{ mA}; V_{CE} = 5\text{ V}$	580	–	700	mV
		$I_C = 10\text{ mA}; V_{CE} = 5\text{ V}$	–	–	770	mV
C_c	collector capacitance	$I_E = i_e = 0; V_{CB} = 10\text{ V}; f = 1\text{ MHz}$	–	–	3	pF
C_e	emitter capacitance	$I_C = i_c = 0; V_{EB} = 500\text{ mV}; f = 1\text{ MHz}$	–	11	–	pF
f_T	transition frequency	$I_C = 10\text{ mA}; V_{CE} = 5\text{ V}; f = 100\text{ MHz}$	100	–	–	MHz
F	noise figure	$I_C = 200\text{ }\mu\text{A}; V_{CE} = 5\text{ V}; R_S = 2\text{ k}\Omega;$ $f = 10\text{ Hz to }15.7\text{ kHz}$	–	–	4	dB
		$I_C = 200\text{ }\mu\text{A}; V_{CE} = 5\text{ V}; R_S = 2\text{ k}\Omega;$ $f = 1\text{ kHz}; B = 200\text{ Hz}$	–	–	4	dB

Note

1. Pulse test: $t_p \leq 300\text{ }\mu\text{s}; \delta \leq 0.02$.

NPN general purpose transistors

BC849W; BC850W



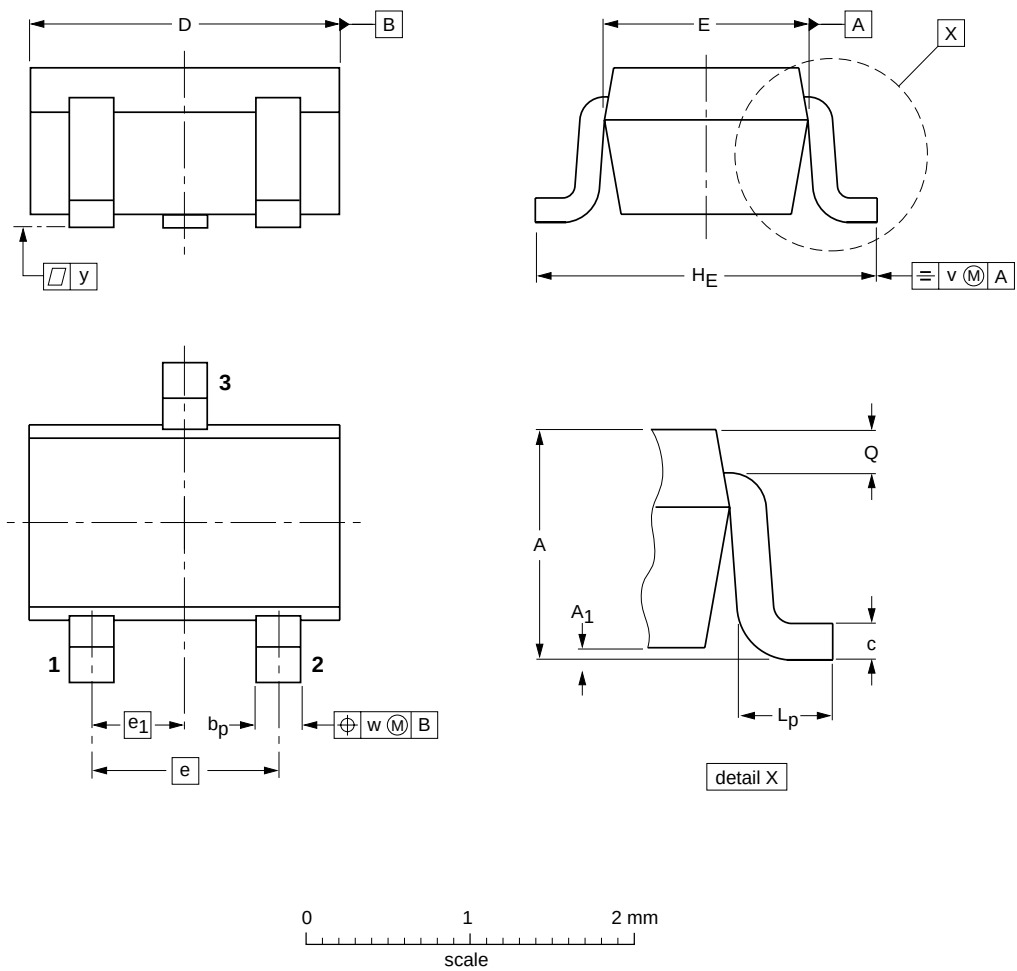
NPN general purpose transistors

BC849W; BC850W

PACKAGE OUTLINE

Plastic surface mounted package; 3 leads

SOT323



DIMENSIONS (mm are the original dimensions)

UNIT	A	A ₁ max	b _p	c	D	E	e	e ₁	H _E	L _p	Q	v	w
mm	1.1 0.8	0.1	0.4 0.3	0.25 0.10	2.2 1.8	1.35 1.15	1.3	0.65	2.2 2.0	0.45 0.15	0.23 0.13	0.2	0.2

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOT323			SC-70			97-02-28

NPN general purpose transistors**BC849W; BC850W****DATA SHEET STATUS**

DOCUMENT STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

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NXP Semiconductors

Customer notification

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